

1.2W AUDIO POWER AMPLIFIER WITH ACTIVE-LOW STANDBY MODE

October 2012

GENERAL DESCRIPTION

The IS31AP4991 has been designed for demanding audio applications such as mobile phones and permits the reduction of the number of external components.

It is capable of delivering 1.2W of continuous RMS output power into an 8Ω load @ 5V.

An externally-controlled standby mode reduces the supply current to much less than $1\mu A$. It also includes internal thermal shutdown protection.

The unity-gain stable amplifier can be configured by external gain setting resistors.

FEATURES

- Operating from V_{CC} = 2.7V ~ 5.5V
- 1.2W output power @ V_{CC} = 5V, THD+N= 1%,
 f = 1kHz, with 8Ω load
- Ultra-low consumption in standby mode (much less than 1µA)
- 65dB PSRR @217Hz in grounded mode
- Near-zero click-and-pop
- Ultra-low distortion (0.025%@0.5W, 1kHz)
- SOP-8 and MSOP-8 package

APPLICATIONS

- Mobile phones
- PDAs
- Portable electronic devices
- Notebook computer

TYPICAL APPLICATION CIRCUIT

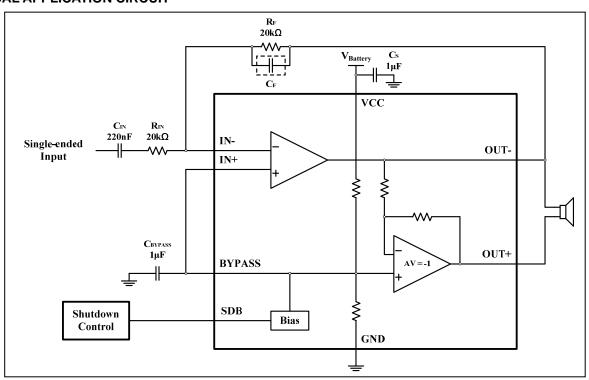


Figure 1 Typical Application Circuit (Single-ended input)

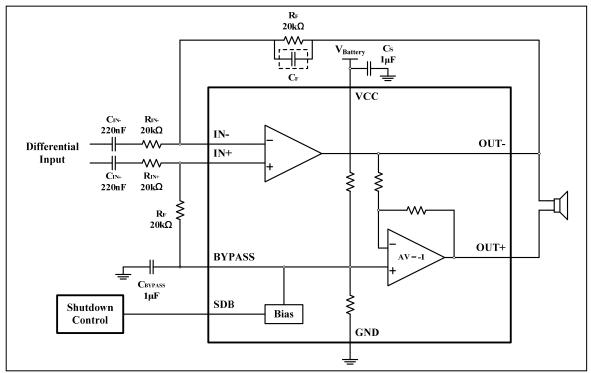


Figure 2 Typical Application Circuit (Differential input)

PIN CONFIGURATION

Package	Pin Configuration (Top View)	
SOP-8	IN+	
MSOP-8	SDB 1 8 OUT+ BYPASS 2 7 GND IN+ 3 6 VCC IN- 4 5 OUT-	

PIN DESCRIPTION

Pin	No.		Description	
FIII	SOP	MSOP	Description	
IN+	1	3	Positive input of the first amplifier.	
OUT-	2	5	Negative output of the IS31AP4991. Connected to the load and to the feedback resistor R_{F} .	
IN-	3	4	Negative input of the first amplifier, receives the audio input signal. Connected to the feedback resistor R_{F} and to the input resistor R_{IN} .	
GND	4	7	Ground.	
BYPASS	5	2	Bypass capacitor pin which provides the common mode voltage ($V_{\text{CC}}/2$).	
OUT+	6	8	Positive output of the IS31AP4991. Connected to the load.	
SDB	7	1	The device enters shutdown mode when a low level is applied on this pin.	
VCC	8	6	Positive analog supply of the chip.	





ORDERING INFORMATION Industrial Range: -40°C to +85°C

Order Part No.	Package	QTY/Reel
IS31AP4991-GRLS2-TR	SOP-8, Lead-free	2500
IS31AP4991-SLS2-TR	MSOP-8, Lead-free	2500

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- b.) the user assume all such risks; and
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ABSOLUTE MAXIMUM RATINGS (Note 1)

Supply voltage, V _{CC}	-0.3V ~ +6.0V
Voltage at any input pin	-0.3V ~ V _{CC} +0.3V
Maximum junction temperature, T _{JMAX}	+150°C
Storage temperature range, T _{STG}	-65°C ~ +150°C
Operating temperature range, T _A	-40°C ~ +85°C

Note 1: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

The following specifications apply for $C_{IN} = 0.22 \mu F$, $R_{IN} = R_F = 20 k\Omega$, $C_{BYPASS} = 1 \mu F$, unless otherwise specified.

Limits apply for $T_A = 25^{\circ}C$. $V_{CC}=5V$ (Note 2 or specified)

Symbol	Parameter	Condition		Тур.	Limit	Unit
I_{CC}	Quiescent power supply current	V_{CC} = 0V, Io = 0A, no I	Load	4.8		mA (max)
I _{STBY}	Standby current	V _{STBY} = GND, R _L = ∞			1	μA(max)
V_{STBYH}	Shutdown voltage input high	V _{CC} = 5.5V			1.4	V(min)
V_{STBYL}	Shutdown voltage input low	V _{CC} = 2.7V			0.4	V(max)
Vos	Output offset voltage				15	mV (max)
Do	Output nouser (00)	THD+N = 1%; f = 1kH	Z	1.18		W
Po	Output power (8Ω)	THD+N = 10%; f = 1kl	Hz	1.46		VV
t _{WU}	Wake-up time (Note 3)	C _{BYPASS} = 1µF		115		ms
THD+N	Total harmonic distortion+noise (Note 3)	Po = 0.5Wrms; f = 1kHz		0.025		%
DCDD	Power supply rejection ratio (Note 3)	I transit Organisate d	f = 217Hz	65		dВ
PSRR			f = 1kHz	77		dB

The following specifications apply for C_{IN} = 0.22 μ F, R_{IN} = R_F = 20 $k\Omega$, C_{BYPASS} = 1 μ F, unless otherwise specified. Limits apply for T_A = 25°C. V_{CC} =3V (Note 2 or specified)

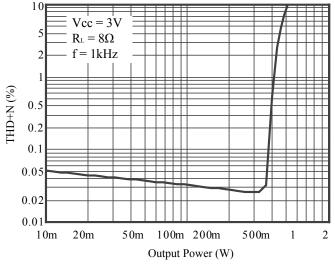
Symbol	Parameter	Condition	Тур.	Limit	Unit
I _{cc}	Quiescent power supply current	V _{CC} = 0V, Io = 0A, no Load	3.8		mA(max)
I _{STBY}	Standby current	V _{STBY} = GND, R _L = ∞		1	μA(max)
Ро	Output power (8Ω)	THD+N = 1%; f = 1kHz	405		mW
		THD+N = 10%; f = 1kHz	502		
t _{wu}	Wake-up time (Note 3)	C _{BYPASS} = 1µF	102		ms
THD+N	Total harmonic distortion+noise (Note 3)	Po = 0.3Wrms; f = 1kHz	0.027		%

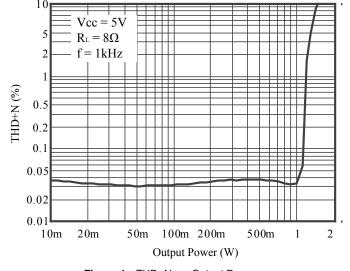
Note 2: Production testing of the device is performed at 25°C. Functional operation of the device and parameters specified over other temperature range, are guaranteed by design, characterization and process control.

Note 3: Guaranteed by design.



TYPICAL PERFORMANCE CHARACTERISTIC







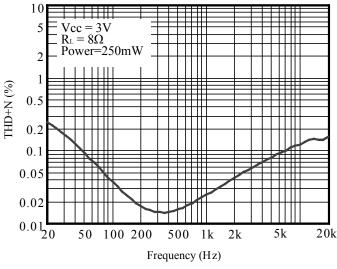


Figure 4 THD+N vs. Output Power

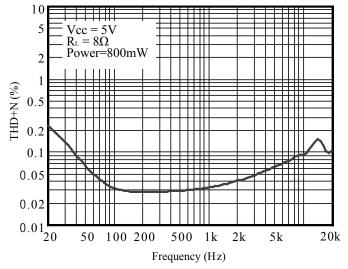


Figure 5 THD+N vs. Frequency

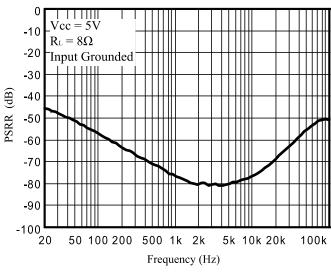


Figure 6 THD+N vs. Frequency

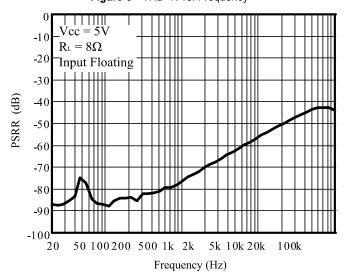
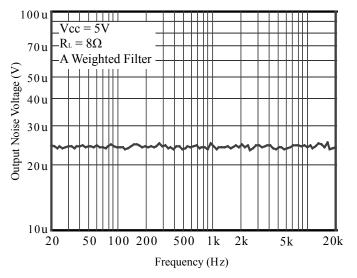


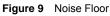
Figure 7 PSRR vs. Frequency

Figure 8 PSRR vs. Frequency

IS31AP4991







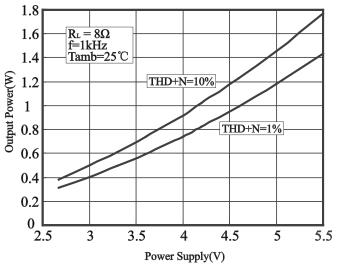


Figure 10 Output Power vs. Power Supply

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APPLICATION INFORMATION

BTL CONFIGURATION PRINCIPLE

The IS31AP4991 is a monolithic power amplifier with a BTL output type. BTL (bridge tied load) means that each end of the load is connected to two single-ended output amplifiers. Thus, we have:

Single-ended output $1 = V_{OUT+} = V_{OUT}(V)$

Single ended output $2 = V_{OUT} = -V_{OUT}(V)$

and

 V_{OUT} + - V_{OUT} - = $2V_{OUT}$ (V)

The output power is:

$$P_{OUT} = \frac{(2V_{OUT_{RMS}})^2}{R_L}$$

For the same power supply voltage, the output power in BTL configuration is four times higher than the output power in single ended configuration.

GAIN IN A TYPICAL APPLICATION SCHEMATIC

The typical application schematic is shown in Figure 1 on page 1.

In the flat region (no C_{IN} effect), the output voltage of the first stage is (in Volts):

$$V_{OUT-} = (-V_{IN}) \frac{R_F}{R_{IN}}$$

For the second stage: $V_{OUT+} = -V_{OUT-}(V)$

The differential output voltage is (in Volts):

$$V_{OUT+} - V_{OUT-} = 2V_{IN} \frac{R_F}{R_{IN}}$$

The differential gain, G_V, is given by:

$$G_{v} = \frac{V_{OUT+} - V_{OUT-}}{V_{IN}} = 2\frac{R_{F}}{R_{IN}}$$

 $V_{\text{OUT-}}$ is in phase with V_{IN} and $V_{\text{OUT+}}$ is phased 180° with V_{IN} . This means that the positive terminal of the loudspeaker should be connected to $V_{\text{OUT+}}$ and the negative to $V_{\text{OUT-}}$.

LOW AND HIGH FREQUENCY RESPONSE

In the low frequency region, C_{IN} starts to have an effect. C_{IN} forms with R_{IN} a high-pass filter with a -3dB cut-off frequency. f_{CL} is in Hz.

$$f_{CL} = \frac{1}{2\pi R_{IN} C_{IN}}$$

In the high frequency region, you can limit the bandwidth by adding a capacitor (C_F) in parallel with R_F . It forms a low-pass filter with a -3dB cut-off frequency.

f_{CH} is in Hz.

$$f_{CH} = \frac{1}{2\pi R_F C_F}$$

DECOUPLING OF THE CIRCUIT

Two capacitors are needed to correctly bypass the IS31AP4991: a power supply bypass capacitor C_S and a bias voltage bypass capacitor C_{BYPASS} .

 $C_{\rm S}$ has particular influence on the THD+N in the high frequency region (above 7kHz) and an indirect influence on power supply disturbances. With a value for $C_{\rm S}$ of 1µF, you can expect THD+N levels similar to those shown in the datasheet.

In the high frequency region, if C_S is lower than $1\mu F$, it increases THD+N and disturbances on the power supply rail are less filtered.

On the other hand, if C_S is higher than $1\mu F$, those disturbances on the power supply rail are more filtered.

C_{BYPASS} has an influence on THD+N at lower frequencies, but its function is critical to the final result of PSRR (with input grounded and in the lower frequency region).

If C_{BYPASS} is lower than 1µF, THD+N increases at lower frequencies and PSRR worsens.

If C_{BYPASS} is higher than 1µF, the benefit on THD+N at lower frequencies is small, but the benefit to PSRR is substantial.

Note that C_{IN} has a non-negligible effect on PSRR at lower frequencies. The lower the value of C_{IN} , the higher the PSRR is.

WAKE-UP TIME (twu)

When the standby is released to put the device on, the bypass capacitor C_{BYPASS} will not be charged immediately. As C_{BYPASS} is directly linked to the bias of the amplifier, the bias will not work properly until the C_{BYPASS} voltage is correct. The time to reach this voltage is called wake-up time or t_{WU} and specified in the electrical characteristics table with $C_{\text{BYPASS}} = 1 \mu F$.

POP PERFORMANCE

Pop performance is intimately linked with the size of the input capacitor C_{IN} and the bias voltage bypass capacitor C_{BYPASS} .

The size of C_{IN} is dependent on the lower cut-off frequency and PSRR values requested. The size of C_{BYPASS} is dependent on THD+N and PSRR values requested at lower frequencies.

Moreover, C_{BYPASS} determines the speed with which the amplifier turns on.



CLASSIFICATION REFLOW PROFILES

Profile Feature	Pb-Free Assembly
Preheat & Soak Temperature min (Tsmin) Temperature max (Tsmax) Time (Tsmin to Tsmax) (ts)	150°C 200°C 60-120 seconds
Average ramp-up rate (Tsmax to Tp)	3°C/second max.
Liquidous temperature (TL) Time at liquidous (tL)	217°C 60-150 seconds
Peak package body temperature (Tp)*	Max 260°C
Time (tp)** within 5°C of the specified classification temperature (Tc)	Max 30 seconds
Average ramp-down rate (Tp to Tsmax)	6°C/second max.
Time 25°C to peak temperature	8 minutes max.

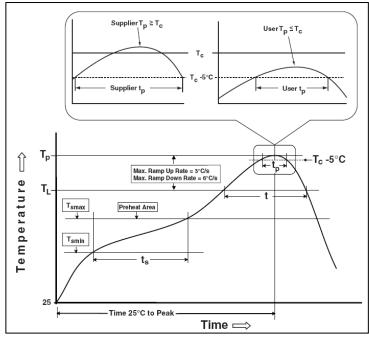
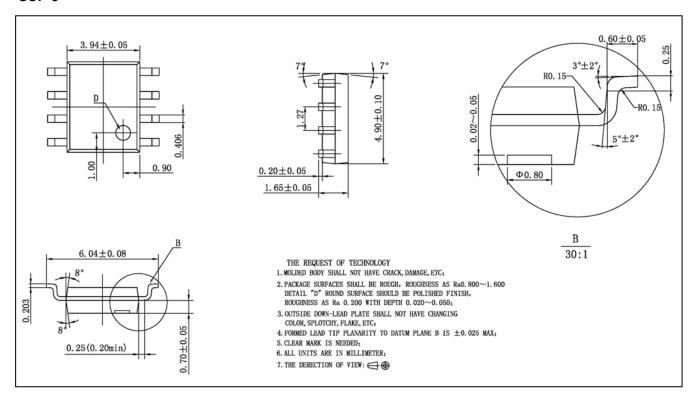


Figure 11 Classification Profile



PACKAGE INFORMATION

SOP-8





MSOP-8

